## **DISCRETE SEMICONDUCTORS**

# DATA SHEET

# **PDTA143E series** PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

Product specification Supersedes data of 2003 Sep 08 2004 Aug 04





### PDTA143E series

#### **FEATURES**

- Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

#### **APPLICATIONS**

- · General purpose switching and amplification
- · Inverter and interface circuits
- · Circuit driver.

#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	_	-50	V
I <sub>O</sub>	output current (DC)	_	-100	mA
R1	bias resistor	4.7	_	kΩ
R2	bias resistor	4.7	_	kΩ

#### **DESCRIPTION**

PNP resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

#### **PRODUCT OVERVIEW**

TYPE NUMBER	PAC	KAGE	MARKING CODE	NPN COMPLEMENT
I TPE NUMBER	PHILIPS	EIAJ	MARKING CODE	NPN COMPLEMENT
PDTA143EE	SOT416	SC-75	01	PDTC143EE
PDTA143EEF	SOT490	SC-89	50	PDTC143EEF
PDTA143EK	SOT346	SC-59	01	PDTC143EK
PDTA143EM	SOT883	SC-101	DL	PDTC143EM
PDTA143ES	SOT54 (TO-92)	SC-43	TA143E	PDTC143ES
PDTA143ET	PDTA143ET SOT23		*01 <sup>(1)</sup>	PDTC143ET
PDTA143EU	SOT323	SC-70	*01 <sup>(1)</sup>	PDTC143EU

#### Note

<sup>1. \* =</sup> p: Made in Hong Kong.

<sup>\* =</sup> t: Made in Malaysia.

<sup>\* =</sup> W: Made in China.

# PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

## PDTA143E series

### SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	CIMPLIFIED OUTLINE AND CYMPOL		PINNING
TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PIN	DESCRIPTION
PDTA143ES	R1	1 2 3	base collector emitter
PDTA143EE PDTA143EEF PDTA143EK PDTA143ET PDTA143EU	3 1 R1 R2 MDB271	1 2 3	base emitter collector
PDTA143EM	2 R1 3 Bottom view ADB267	1 2 3	base emitter collector

## PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

### PDTA143E series

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	-10	V
V <sub>I</sub>	input voltage				
	positive		_	+10	V
	negative		_	-30	V
Io	output current (DC)		_	-100	mA
I <sub>CM</sub>	peak collector current		_	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT23	note 1	_	250	mW
	SOT54	note 1	_	500	mW
	SOT323	note 1	_	200	mW
	SOT346	note 1	_	250	mW
	SOT416	note 1	_	150	mW
	SOT490	notes 1 and 2	_	250	mW
	SOT883	notes 2 and 3	_	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### **Notes**

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μm copper strip line.

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air		
	SOT23	note 1	500	K/W
	SOT54	note 1	250	K/W
	SOT323	note 1	625	K/W
	SOT346	note 1	500	K/W
	SOT416	note 1	833	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W

#### **Notes**

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

# PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

# PDTA143E series

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0$	_	_	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_{B} = 0$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_{B} = 0; T_{j} = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-0.9	mA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}$	30	_	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	_	-150	mV
$V_{i(off)}$	input-off voltage	$I_C = -100 \mu\text{A};  V_{CE} = -5 \text{V}$	_	-1.1	-0.5	V
V <sub>i(on)</sub>	input-on voltage	$I_C = -20 \text{ mA}; V_{CE} = -0.3 \text{ V}$	-2.5	-1.9	_	V
R1	input resistor		3.3	4.7	6.1	kΩ
R2 R1	resistor ratio		0.8	1	1.2	
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = -10 \text{ V}$ ; $f = 1 \text{ MHz}$	_	_	3	pF

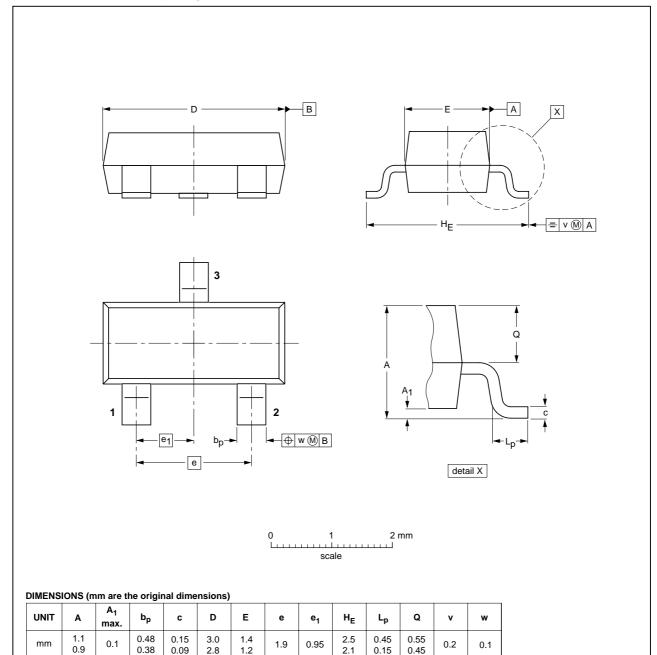
# PNP resistor-equipped transistors; $R1 = 4.7 \text{ k}\Omega$ , $R2 = 4.7 \text{ k}\Omega$

## PDTA143E series

#### **PACKAGE OUTLINES**

### Plastic surface mounted package; 3 leads

SOT23



OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT23		TO-236AB				<del>-97-02-28-</del> 99-09-13	

2004 Aug 04 6

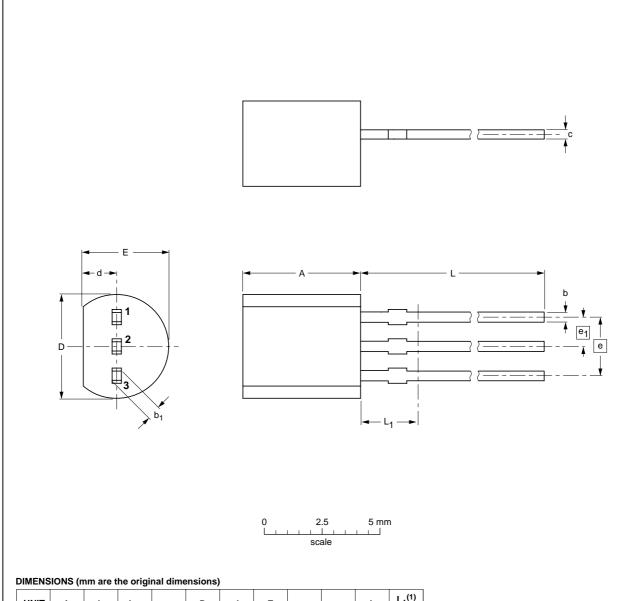
0.38

# PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

## PDTA143E series

### Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	A	b	b <sub>1</sub>	С	D	d	E	е	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup> max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

#### Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

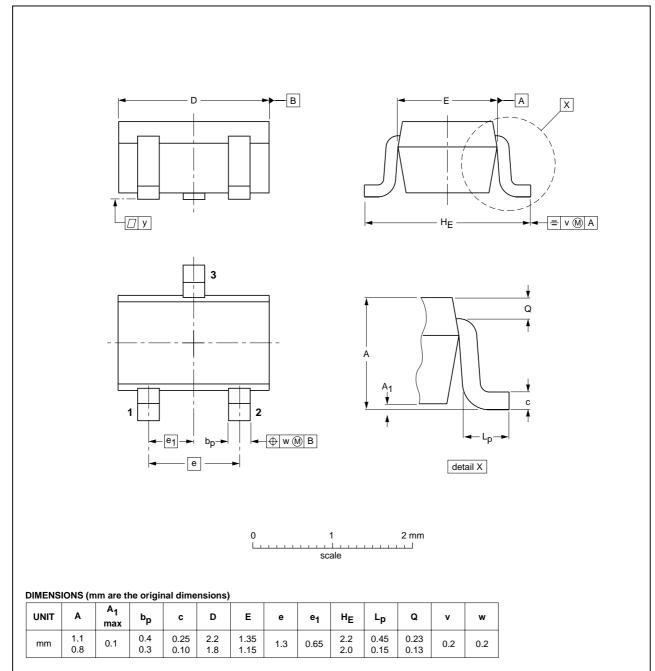
OUTLINE		REFER	ENCES	EUROPEAN		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT54		TO-92	SC-43A			<del>97-02-28</del> 04-06-28

# PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

## PDTA143E series

### Plastic surface mounted package; 3 leads

**SOT323** 

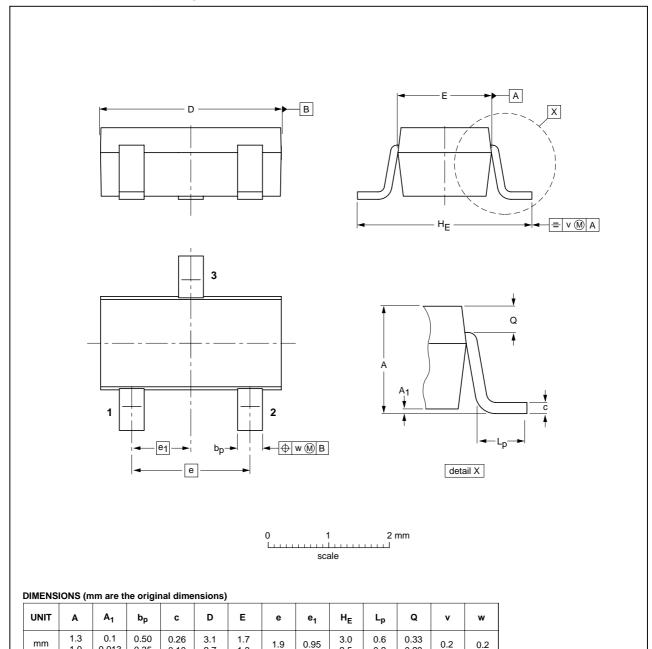


OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT323			SC-70	_		97-02-28

## PDTA143E series

### Plastic surface mounted package; 3 leads

**SOT346** 



OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT346		TO-236	SC-59		$\bigoplus \bigoplus$	98-07-17	

2004 Aug 04 9

1.0

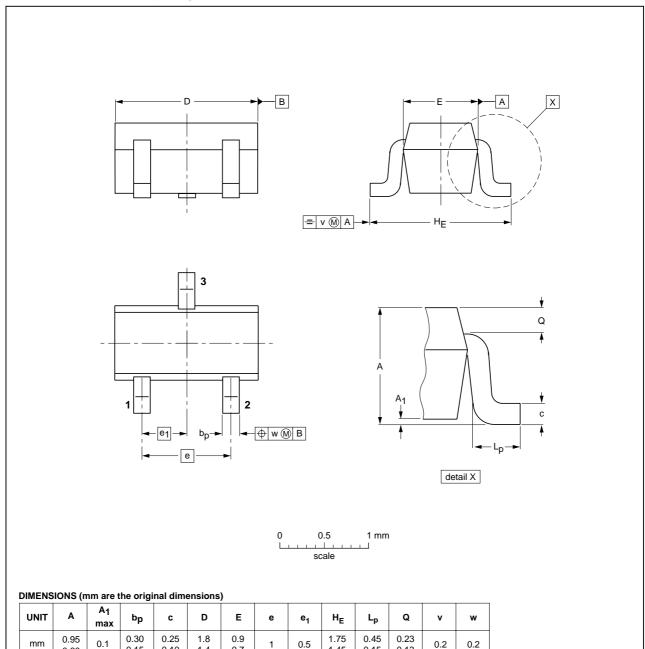
0.013

0.35

## PDTA143E series

### Plastic surface mounted package; 3 leads

**SOT416** 



OUTLINE VERSION		REFER	EUROPEAN	ISSUE DATE		
	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT416			SC-75			97-02-28

1.45

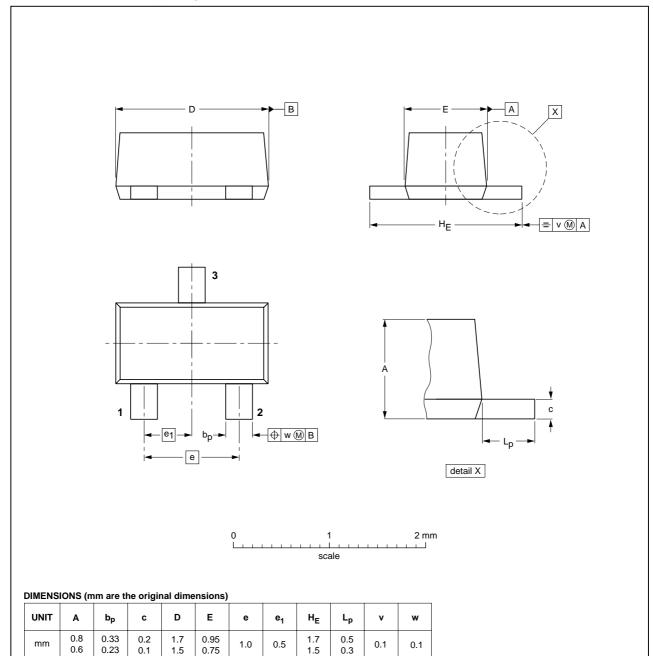
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0.10

## PDTA143E series

### Plastic surface mounted package; 3 leads

SOT490

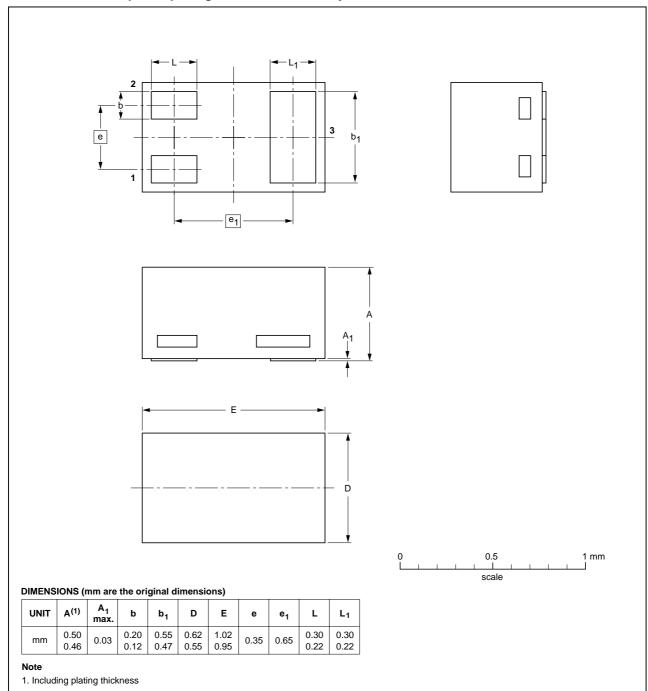


VERSION IEC JEDEC EIAJ PROJECTION	OUTLINE		REFERENCES				ISSUE DATE
	VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
	SOT490			SC-89			98-10-23

## PDTA143E series

### Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

**SOT883** 



OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT883			SC-101			<del>03-02-05</del> 03-04-03

## PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

### PDTA143E series

#### **DATA SHEET STATUS**

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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